# **2-Input NAND Gate**

The MC74VHC1G00 is an advanced high speed CMOS 2–input NAND gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The MC74VHC1G00 input structure provides protection when voltages up to 7V are applied, regardless of the supply voltage. This allows the MC74VHC1G00 to be used to interface 5V circuits to 3V circuits.

- High Speed:  $t_{PD} = 3.0$ ns (Typ) at  $V_{CC} = 5V$
- Low Power Dissipation:  $I_{CC} = 2\mu A$  (Max) at  $T_A = 25^{\circ}C$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V; MM > 200V, CDM > 1500V

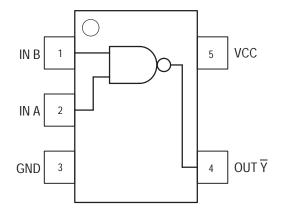


Figure 1. 5-Lead SOT-353 Pinout (Top View)

#### LOGIC SYMBOL





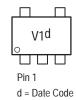
## **ON Semiconductor**

Formerly a Division of Motorola http://onsemi.com



SC-88A / SOT-353 DF SUFFIX CASE 419A

#### MARKING DIAGRAM



	PIN ASSIGNMENT
1	IN B
2	IN A
3	GND
4	OUT Y
5	VCC

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

#### **FUNCTION TABLE**

Inp	uts	Output
А	В	Ŧ
L	L	Н
L	н	Н
Н	L	Н
Н	Н	L

© Semiconductor Components Industries, LLC, 1999 **December, 1999 – Rev. 2** 

#### **MAXIMUM RATINGS\***

Characteristics	Symbol	Value	Unit
DC Supply Voltage	V <sub>CC</sub>	-0.5 to +7.0	V
DC Input Voltage	V <sub>IN</sub>	-0.5 to +7.0	V
DC Output Voltage V <sub>CC</sub> = 0 High or Low State	Vout	−0.5 to 7.0 −0.5 to V <sub>CC</sub> + 0.5	V
Input Diode Current	lik	-20	mA
Output Diode Current $(V_{OUT} < GND; V_{OUT} > V_{CC})$	Іок	+20	mA
DC Output Current, per Pin	lout	+25	mA
DC Supply Current, $V_{CC}$ and GND	Icc	+50	mA
Power dissipation in still air, SC-88A †	PD	200	mW
Lead temperature, 1 mm from case for 10 s	TL	260	°C
Storage temperature	T <sub>stg</sub>	-65 to +150	°C

\* Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — SC–88A Package: –3 mW/°C from 65° to 125°C

#### **RECOMMENDED OPERATING CONDITIONS**

Characteristics	Symbol	Min	Max	Unit
DC Supply Voltage	VCC	2.0	5.5	V
DC Input Voltage	VIN	0.0	5.5	V
DC Output Voltage	VOUT	0.0	V <sub>CC</sub>	V
Operating Temperature Range	TA	-55	+85	°C
Input Rise and Fall Time $V_{CC} = 3.3V \pm 0.3V$ $V_{CC} = 5.0V \pm 0.5V$	t <sub>r</sub> , t <sub>f</sub>	0 0	100 20	ns/V

			Vcc	ר	A = 25°	C	T <sub>A</sub> ≤	85°C	<b>TA</b> ≤ '	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
VIH	Minimum High–Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
VIL	Maximum Low–Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
V <sub>OH</sub>	Minimum High–Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50\mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4mA$ $I_{OH} = -8mA$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V <sub>OL</sub>	Maximum Low–Level Output Voltage VIN = VIH or VIL	VIN = VIH or VIL IOL = 50μA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4mA$ $I_{OL} = 8mA$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
ICC	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	μA

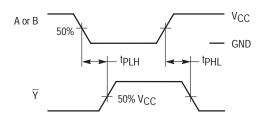
#### DC ELECTRICAL CHARACTERISTICS

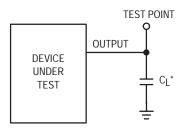
#### **AC ELECTRICAL CHARACTERISTICS** ( $C_{load} = 50 \text{ pF}$ , Input $t_r = t_f = 3.0 \text{ns}$ )

					A = 25°	C	T <sub>A</sub> ≤	85°C	<b>TA</b> ≤ <i>'</i>	125°C	
Symbol	Parameter	Test Condi	itions	Min	Тур	Max	Min	Max	Min	Мах	Unit
<sup>t</sup> PLH <sup>,</sup> <sup>t</sup> PHL	Maximum Propogation Delay,	$V_{CC} = 3.0 \pm 0.3 V$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		4.5 5.6	7.9 11.4		9.5 13.0		11.0 15.5	ns
	Input A or B to Y	$V_{CC} = 5.0 \pm 0.5 V$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		3.0 3.8	5.5 7.5		6.5 8.5		8.0 10.0	
C <sub>IN</sub>	Maximum Input Capacitance				5.5	10		10		10	pF
							pical @	25°C, V	CC = 5.0	ov 🛛	
Coo	Power Dissipation Capa	citance (Note 1.)						10			nF

 Image: CPD
 Power Dissipation Capacitance (Note 1.)
 Image: rypical @ 25°C, V<sub>CC</sub> = 5.0V
 pF

 1.
 CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC}(OPR) = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC} \cdot C_{PD}$  is used to determine the no–load dynamic power consumption;  $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$ .





\*Includes all probe and jig capacitance

#### Figure 3. Test Circuit

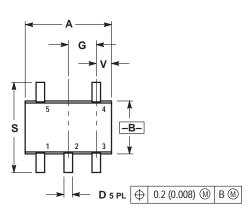
#### Figure 2. Switching Waveforms

#### **DEVICE ORDERING INFORMATION**

			Device Nome	enclature	-			
Device Order Number	Circuit Indicator	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape & Reel Suffix	Package Type	Tape and Reel Size
MC74VHC1G00DFT1	MC	74	VHC1G	00	DF	T1	SC-88A / SOT-353	7–Inch/3000 Unit

#### PACKAGE DIMENSIONS

SC-88A / SOT-353 **DF SUFFIX** 5-LEAD PACKAGE CASE 419A-01 ISSUE B

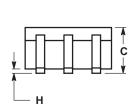


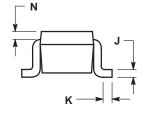
### NOTES:

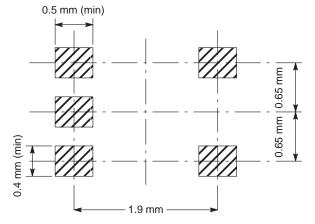
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. N: MM.

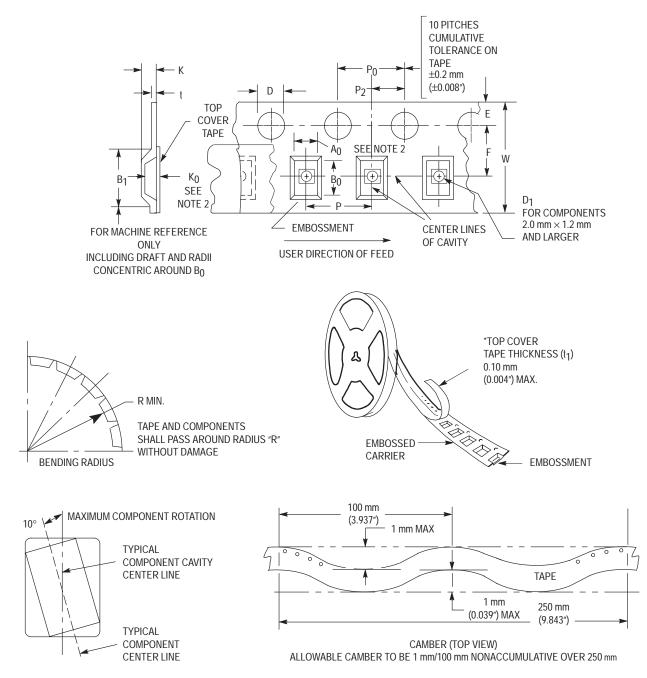
2. CONTROLLING DIMENSION
--------------------------

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65	BSC
Н		0.004		0.10
J	0.004	0.010	0.10	0.25
К	0.004	0.012	0.10	0.30
Ν	0.008	REF	0.20	REF
S	0.079	0.087	2.00	2.20
V	0.012	0.016	0.30	0.40











Tape Size	B <sub>1</sub> Max	D	D <sub>1</sub>	Е	F	к	Р	P <sub>0</sub>	P <sub>2</sub>	R	т	w
8 mm	4.35 mm (0.171″)	1.5 +0.1/ -0.0 mm (0.059 +0.004/ -0.0")	1.0 mm Min (0.039")	1.75 ±0.1 mm (0.069 ±0.004″)	3.5 ±0.5 mm (1.38 ±0.002")	2.4 mm (0.094")	4.0 ±0.10 mm (0.157 ±0.004")	4.0 ±0.1 mm (0.156 ±0.004")	2.0 ±0.1 mm (0.079 ±0.002")	25 mm (0.98")	0.3 ±0.05 mm (0.01 +0.0038/ -0.0002")	8.0 ±0.3 mm (0.315 ±0.012")

EMBOSSED	CARRIER	DIMENSIONS	(See	Notes	1	and 2)	١
LINDUSSED	CANNEN	DIVILIAGIONO	0000	110163		and $z$	1

1. Metric Dimensions Govern-English are in parentheses for reference only.

2. A<sub>0</sub>, B<sub>0</sub>, and K<sub>0</sub> are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

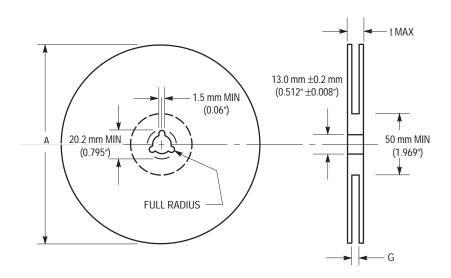
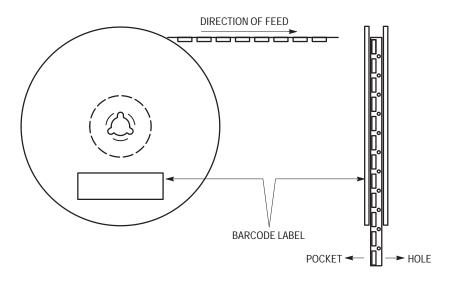


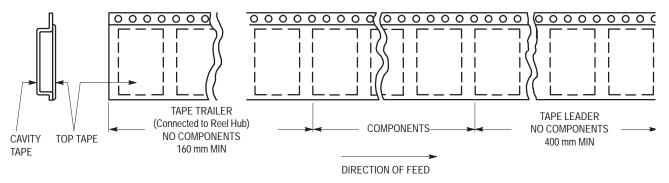
Figure 5. Reel Dimensions

#### **REEL DIMENSIONS**

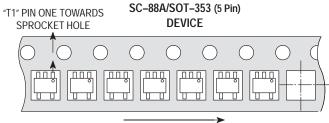
Tape Size	A Max	G	t Max
8 mm	330 mm	8.400 mm, +1.5 mm, -0.0	14.4 mm
	(13")	(0.33", +0.059", -0.00)	(0.56″)











User Direction of Feed

Figure 8. Reel Configuration

**ON Semiconductor** and without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

#### PUBLICATION ORDERING INFORMATION

#### USA/EUROPE Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: ONlit@hibbertco.com

Fax Response Line\*: 303–675–2167 800–344–3810 Toll Free USA/Canada \*To receive a Fax of our publications

N. America Technical Support: 800-282-9855 Toll Free USA/Canada

ASIA/PACIFIC: LDC for ON Semiconductor – Asia Support Phone: 303–675–2121 (Tue–Fri 9:00am to 1:00pm, Hong Kong Time) Email: ONlit–asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–8549 Phone: 81–3–5487–8345 Email: r14153@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local Sales Representative.